

PCT
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

PCT

OLIVIER MARTY et al.

Serial No. 10/512,077 ✓

Filed: November 5, 2004

For: PROCESS FOR MODIFYING THE PROPERTIES OF A THIN LAYER AND SUBSTRATE APPLYING SAID PROCESS

INFORMATION DISCLOSURE STATEMENT

Honorable Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

Sir:

Applicants submit herewith the International Search Report of the corresponding PCT application, together with a Form PTO-1449 and copies of the references cited therein.

Respectfully submitted,

Ira J. Schultz
Registration No. 28666

Form PTO-1449

ATTY DOCKET NO.
04202APPLICATION
NO. 10/512,077INFORMATION DISCLOSURE CITATION
IN AN APPLICATION

(Use several sheets if necessary)

APPLICANT
Olivier Marty et al.FILING DATE
November 5, 2004

GROUP

U.S. PATENT DOCUMENTS

| EXAMINER INITIAL | DOCUMENT NUMBER | | | | | | | DATE | NAME | CLASS | SUB CLASS | FILING DATE IF APPROPRIATE |
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FOREIGN PATENT DOCUMENTS

| | DOCUMENT NUMBER | | | | | | | DATE | COUNTRY | CLASS | SUB CLASS | TRANSLATION | |
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| | | | | | | | | | | | | YES | NO |
| | 10 | 2 | 5 | 8 | 2 | 7 | 3 | 3/00 | EP Abstract | | | | |
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| | Sanchez et al, "Structural and Morphological Characteristics of InGaAs/GaAs Quantum Well Structures on Tilted (111)BGaAs Grown by MBE", Journal of Crystal Growth etc., Vol. 192, No. 3-4, Sept. 1, 1998, pp 363-371. |
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EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.